



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92 Plastic-Encapsulate Transistors

2SA1625 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 750 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -0.5 A

Collector-base voltage

$V_{(BR)CBO}$: -400 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-92

1. EMITTER
2. COLLECTOR
3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-400			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-1mA, I_B=0$	-400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-400V, I_E=0$			-1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-5V, I_C=0$			-1	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-50mA$	40		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-100mA, I_B=-10mA$			-1	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=-100mA, I_B=-10mA$			-1.2	V
Transition frequency	f_T	$V_{CE}=-10V, I_C=-10mA$		10		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$	20	40		pF
Turn-on Time	t_{on}	$V_{CC}=-150V, I_C=-100mA,$ $I_{B1}=I_{B2}-10mA, R_L=1.5K\Omega$		1		μs
Storage Time	t_{stg}			5		μs
Fall-Time	t_f			1		μs

CLASSIFICATION OF $h_{FE(1)}$

Rank	M	L	K
Range	40-80	60-120	100-200